

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE8295AD uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

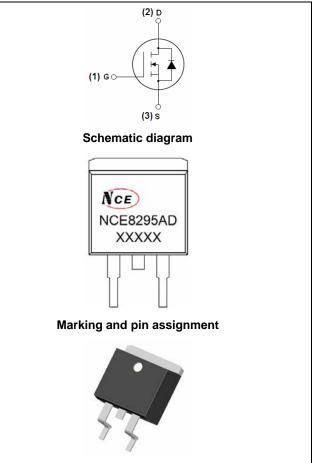
General Features

- V_{DS} =82V,I_D =95A
 - $R_{DS(ON)} < 8.0 \text{ m}\Omega @ V_{GS}=10V$ (Typ:6.6m Ω)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Special designed for convertors and power controls
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

100% UIS TESTED! 100% ΔVds TESTED!



TO-263-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE8295AD	NCE8295AD	TO-263-2L	-	-	-

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	82	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	95	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	67	A
Pulsed Drain Current	I _{DM}	320	A
Maximum Power Dissipation	PD	170	W
Derating factor		1.13	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	529	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	0.88	°C /W	
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Electrical Characteristics (T_A=25 $^\circ\!\mathrm{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·····		•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	82	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =82V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2	2.9	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	6.6	8.0	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A	-	50	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	V _{DS} =25V,V _{GS} =0V,	-	6800	-	PF
Output Capacitance	C _{oss}		-	353	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	261	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	18	-	nS
Turn-on Rise Time	tr	VDD=40V,RL=15Ω RG=2.5Ω,VGS=10V	-	12	-	nS
Turn-Off Delay Time	t _{d(off)}		-	56	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Qg	V _{DS} =40V,I _D =50A,	-	109.3	-	nC
Gate-Source Charge	Q _{gs}		-	35.1	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	25.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =95A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	95	A
Reverse Recovery Time	t _{rr}	Tj=25℃,I _F =100A	-		37	nS
Reverse Recovery Charge	Qrr	di/dt=100A/µs ^(Note3)	-		58	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

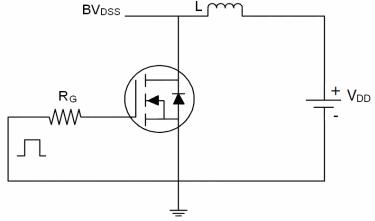
4. Guaranteed by design, not subject to production

5. EAS condition: Tj=25 $^{\circ}$ C,V_{DD}=40V,V_G=10V,L=0.5mH,Rg=25 Ω

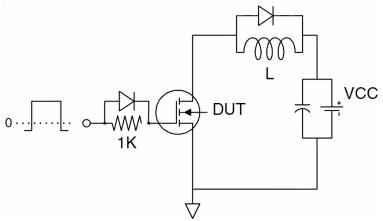


Test Circuit

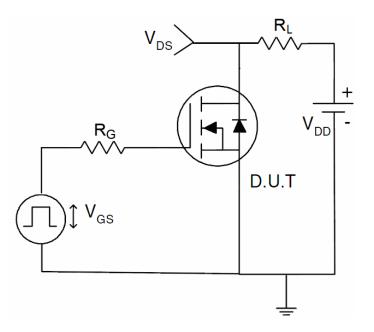
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit

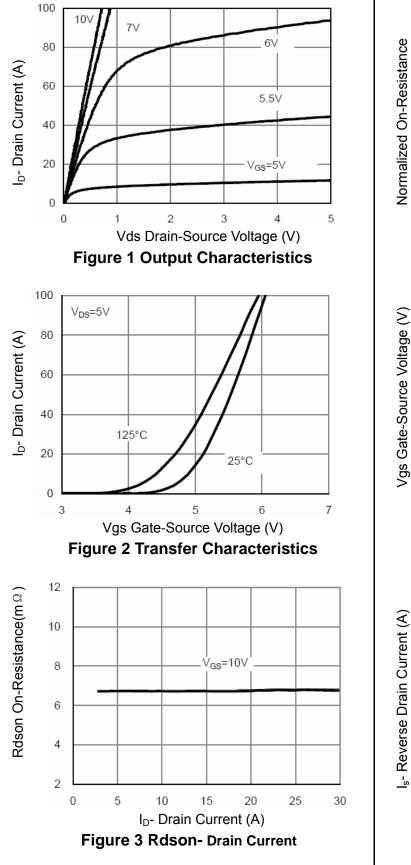


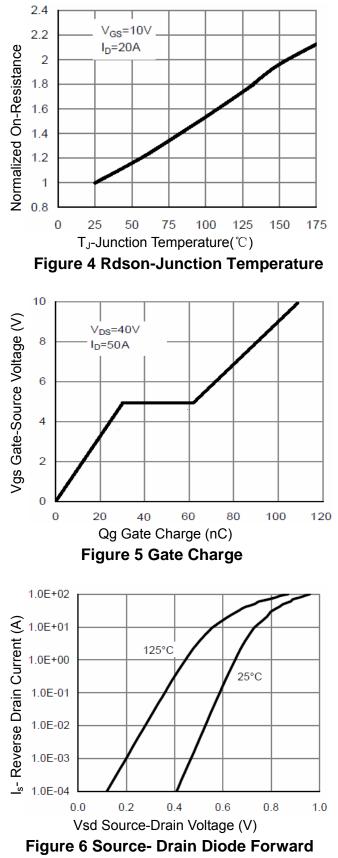
3) Switch Time Test Circuit





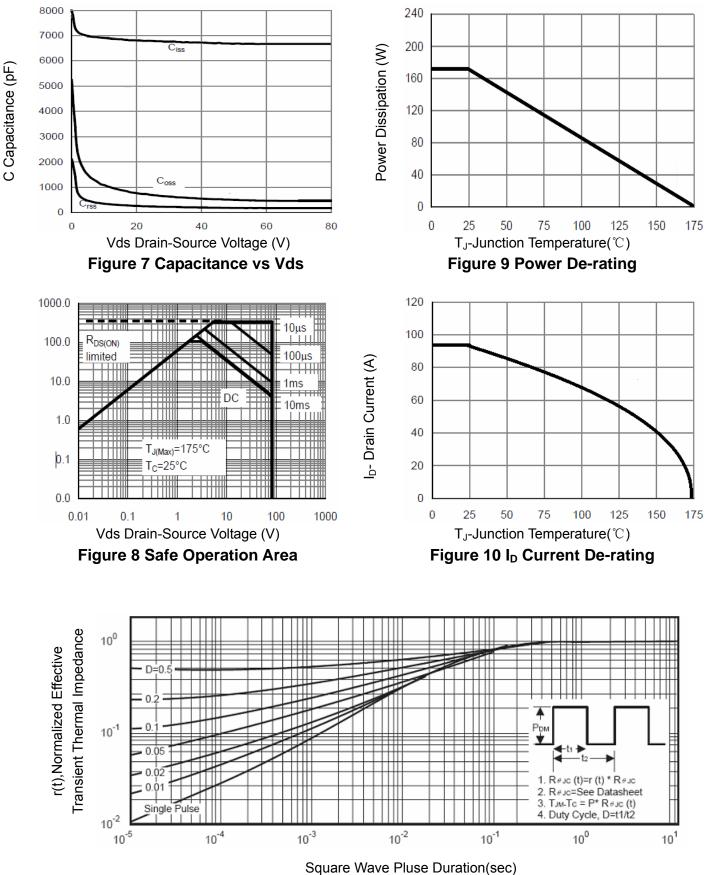
Typical Electrical and Thermal Characteristics (Curves

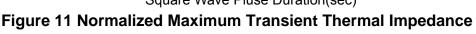






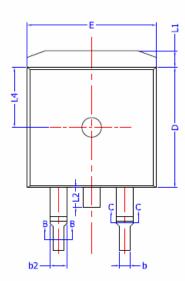
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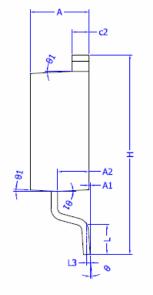


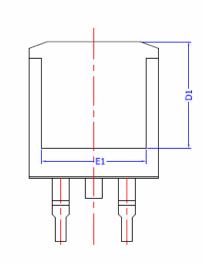


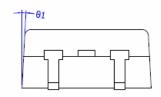


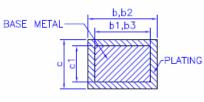
TO-263-2L Package Information











SECTION B-B&C-C

(UNITS OF MEASURE =MILLIMETER)				
SYMBOL	MIN	NOM	MAX	
Α	4.40	4.50	4.60	
A1	0	0.10	0.25	
A2	2,20	2,40	2,60	
b	0,76		0,89	
b1	0,75	0,80	0,85	
b2	1,23	—	1,37	
b3	1,22	1,27	1,32	
с	0,47	—	0,60	
c1	0.46	0.51	0.56	
c2	1,25	1.30	1,35	
D	9,10	9,20	9,30	
D1	8.00		—	
E	9.80	9,90	10.00	
E1	7.80	—	—	
е	2.54 BSC			
Н	14.90	15.30	15,70	
L L1	2.00	2,30	2,60	
L1	1.17	1.27	1.40	
L2			1,75	
L3	0.25BSC			
L4	4.60 REF			
θ	0°		8°	
θ1	1°	3°	5°	

COMMON DIMENSIONS JNITS OF MEASURE =MILLIMETER)



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